





SB2060 SCHOTTKY RECTIFIER



Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters,
 Free Wheeling, and Polarity Protection Applications
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- · Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Disk drives
- Battery charging

Maximum Ratings:

| Characteristics | Symbol | Condition | Max. | Units |
|--|--|--|------|-------|
| Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage | V _{RRM} V _{RWM} V _R | - | 60 | V |
| Average Rectified Forward Current | I _{F (AV)} | 50% duty cycle @T _C =135°C, rectangular wave form | 20 | Α |
| Peak One Cycle Non-Repetitive Surge Current | I _{FSM} | 8.3 ms, half Sine pulse, T _C =25°C | 300 | Α |

Electrical Characteristics:

| Characteristics | Symbol | Condition | Тур. | Max. | Units |
|------------------------|-----------------|--|------|--------|-------|
| Forward Voltage Drop* | V _{F1} | V _{F1} @ 20A, Pulse, T _J = 25 °C | | 0.70 | V |
| | V _{F2} | @ 20A, Pulse, T _J = 125 °C | 0.57 | 0.60 | V |
| Reverse Current* | I _{R1} | I _{R1} @V _R = Rated V _R , Pulse, T _J = 25 °C | | 1.0 | mA |
| | I _{R2} | @V _R = Rated V _R , Pulse, T _J = 125 °C | 24 | 40 | mA |
| Junction Capacitance | Ст | @V _R = 5V, T _C = 25 °C, f _{SIG} = 1MHz | 616 | 900 | pF |
| Voltage Rate of Change | dv/dt | - | - | 10,000 | V/us |

^{*} Pulse width < 300 µs, duty cycle < 2%



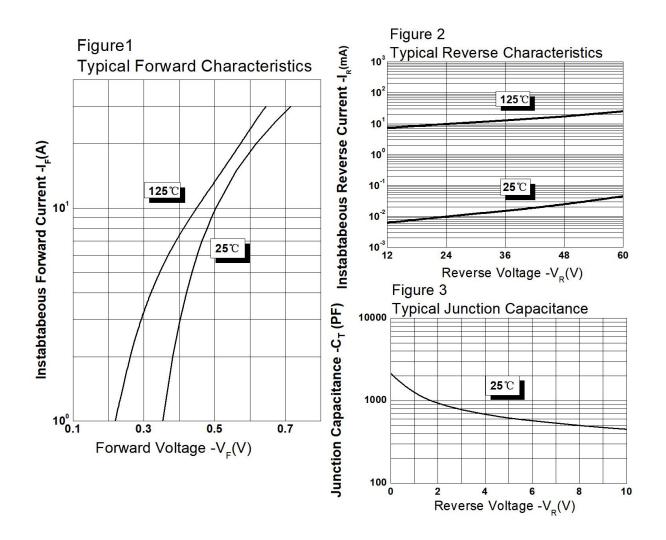




Thermal-Mechanical Specifications:

| Characteristics | Symbol | Condition | Specification | Units |
|---|----------------|--------------|---------------|-------|
| Junction Temperature | TJ | - | -55 to +150 | °C |
| Storage Temperature | T_{stg} | - | -55 to +150 | °C |
| Typical Thermal Resistance Junction to Case | $R_{	heta JC}$ | DC operation | 2 | °C/W |
| Approximate Weight | wt | - | 1.02 | g |

Ratings and Characteristics Curves



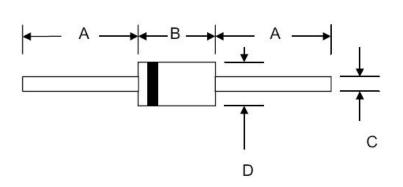
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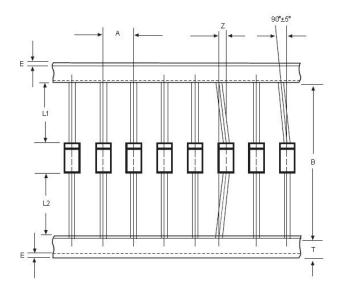


Mechanical Dimensions DO-201AD



| OVMDOL | Millimeters | | Inches | | |
|--------|-------------|------|--------|-------|--|
| SYMBOL | Min. | Max. | Min. | Max. | |
| А | 25.4 | - | 1.000 | - | |
| В | 8.50 | 9.50 | 0.335 | 0.374 | |
| С | 1.2 | 1.3 | 0.048 | 0.052 | |
| D | 5.0 | 5.6 | 0.197 | 0.220 | |

Carrier Tape Specification DO-201AD



| SYMBOL | Millimeters | | |
|---------|-------------|-------|--|
| STWIBOL | Min. | Max. | |
| А | 9.50 | 10.50 | |
| В | 50.9 | 53.9 | |
| Z | - | 1.20 | |
| Т | 5.60 | 6.40 | |
| E | - | 0.80 | |
| IL1-L2I | - | 1.0 | |

Ordering Information

| Device | Package | Shipping |
|--------|-----------|-----------------|
| SB2060 | DO-201AD | 10500000 / 4000 |
| | (Pb-Free) | 1250pcs / tape |

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



Where XXXXX is YYWWL

 SB2060
 = Part Name

 SSG
 = SSG

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

- China Germany Korea Singapore United States
 - http://www.smc-diodes.com sales@ smc-diodes.com •







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